



## SOT-23 Plastic-Encapsulated Diodes

### BAS19LT1 SWITCHING DIODE

#### FEATURES

Power dissipation

$P_D$ : 225 mW ( $T_{amb}=25^\circ\text{C}$ )

Forward Current

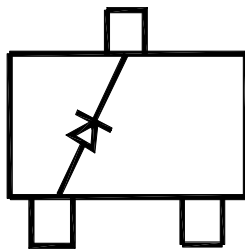
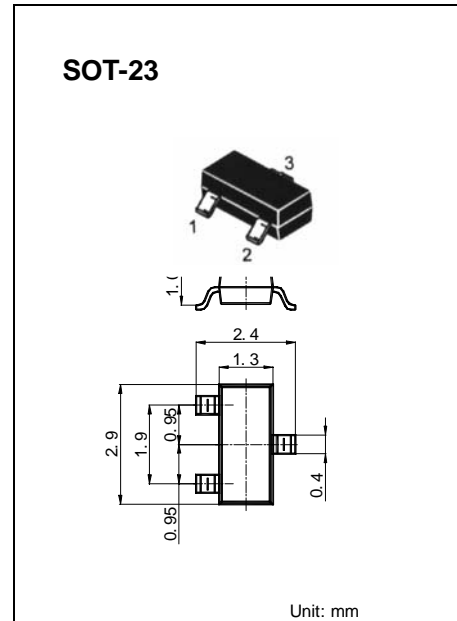
$I_F$ : 200 mA

Reverse Voltage

$V_R$ : 120 V

Operating and storage junction temperature range

$T_J, T_{stg}$ :  $-55^\circ\text{C}$  to  $+150^\circ\text{C}$



Marking JP

#### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	120		V
Reverse voltage leakage current	$I_R$	$V_R=100\text{V}$		0.1	$\mu\text{A}$
Forward voltage	$V_F$	$I_F=100\text{mA}$ $I_F=200\text{mA}$		1000 1250	mV
Diode capacitance	$C_D$	$V_R=0\text{V}, f=1\text{MHz}$		5	pF
Reverse recovery time	$t_{rr}$			50	nS